

■ PRODUCT CHARACTERISTICS

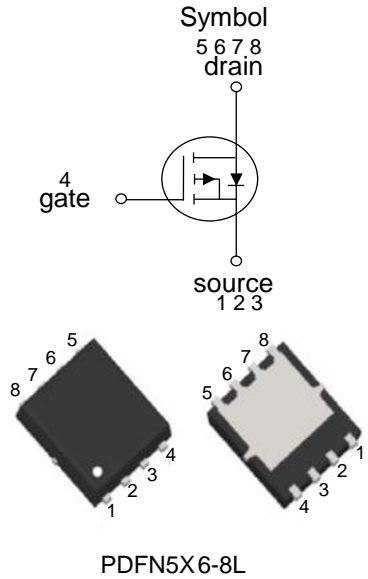
V _{DSS}	-30V
R _{DS(on)} Typ(@V _{GS} =-4.5V)	14mΩ
R _{DS(on)} Typ(@V _{GS} =-10V)	9.5mΩ
I _D	-20A

■ APPLICATIONS

- PWM applications
- Load switch
- Power management

■ FEATURES

- High power and current handling capability
- Led free product is acquired
- Surface mount package



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-free	Halogen		
N/A	MOT3712G	PDFN5X6-8L	5000pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS(T_C=25°C , unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DSS}	-30	V
Gate-source voltage	V _{GSS}	±20	V
Drain current	I _D	-20	A
Pulsed drain current	I _{DM}	-80	A
Power dissipation	P _D	35	W
Junction temperature	T _J	+150	°C
Storage temperature	T _{STG}	-55~+150	°C

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250uA	-30	-	-	V
Drain-source leakage current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	-1	μA
Gate-source leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	100	nA
On characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _{DS} =-250uA	-1.2	-	-2.5	V
On-state characteristics	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-15A	-	14	18	mΩ
		V _{GS} =-10V, I _D =-15A	-	9.5	12	mΩ
Forward transconductance	g _{FS}	V _{DS} =-5V, I _D =-15A	10	-	-	S
Dynamic characteristics						
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-25V f=1MHz	-	2130	-	pF
Out capacitance	C _{oss}		-	302	-	pF
Reverse transfer capacitance	C _{rss}		-	227	-	pF
Switching characteristics						
Total gate charge	Q _g	V _{GS} =-10V, V _{DS} =-15V I _D =-20A	-	10	-	nC
Gate-source charge	Q _{gs}		-	2	-	nC
Gate-drain charge	Q _{gd}		-	2.7	-	nC
Turn-on delay time	t _{d(on)}	V _{DD} =-15V, I _D =-15A R _G =1 V _{GS} =-10V	-	12	-	nS
Turn-on rise time	t _r		-	10	-	nS
Turn-off delay time	t _{d(off)}		-	25	-	nS
Turn-off fall time	t _f		-	13	-	nS
Source-drain diode ratings and characteristics						
Continuous diode forward current	I _{SD}		-	-	-20	A
Diode forward current	V _{SD}	V _{GS} =0V, I _{SD} =-20A	-	-	-1.2	V

■ TYPICAL CHARACTERISTICS

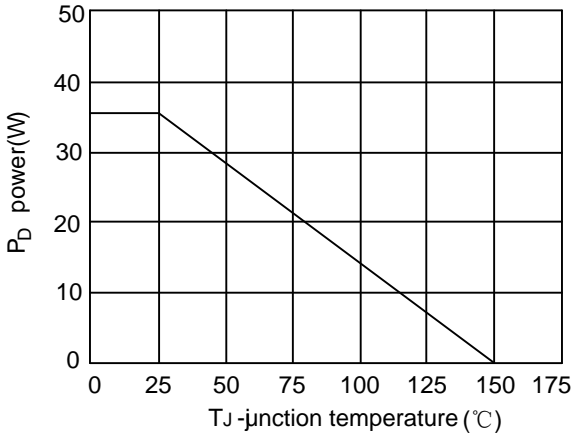


Fig.1 power dissipation

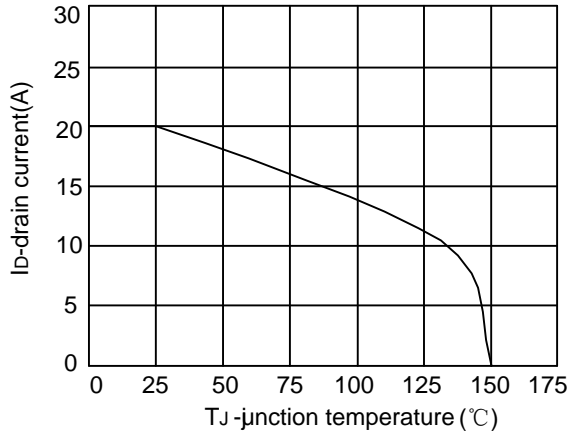


Fig.2 current vs junction temperature

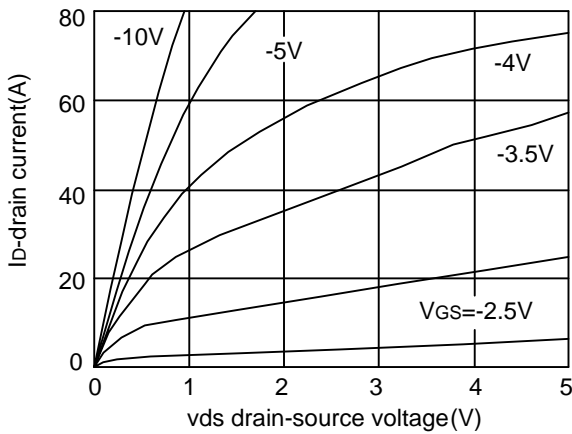


Fig.3 output characteristics

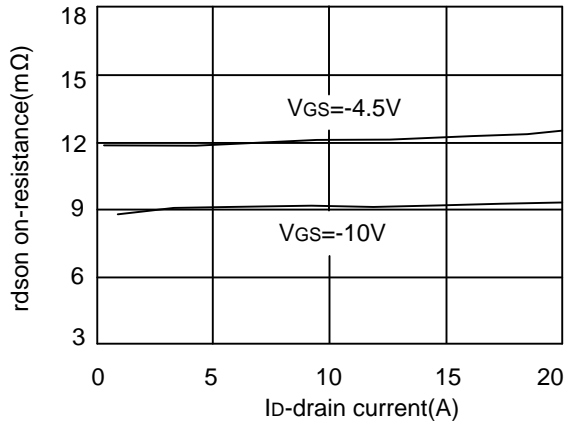


Fig.4 drain-source on-resistance

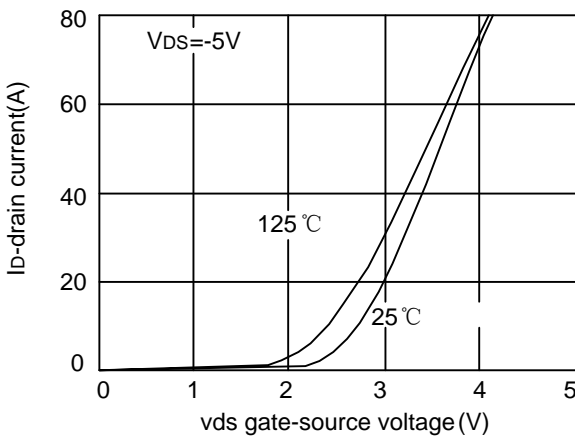


Fig.5 transfer characteristics

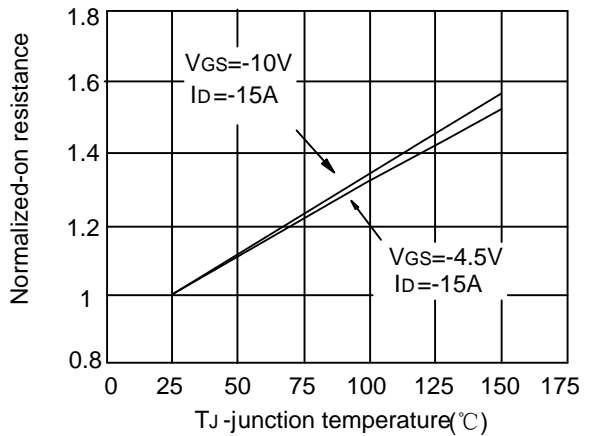


Fig.6 drain-source on-resistance

■ TYPICAL CHARACTERISTICS(Cont.)

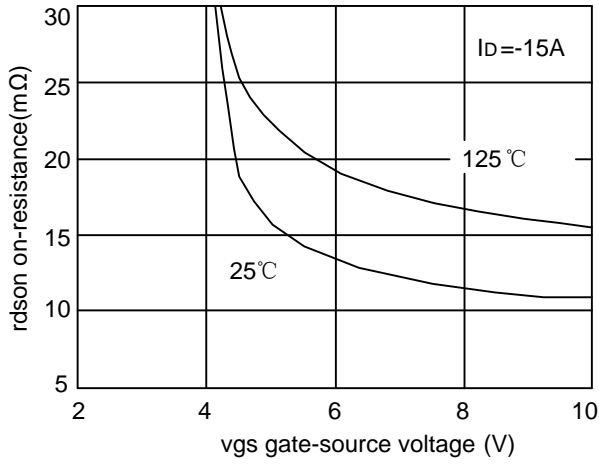


Fig.7 rdson vs vgs

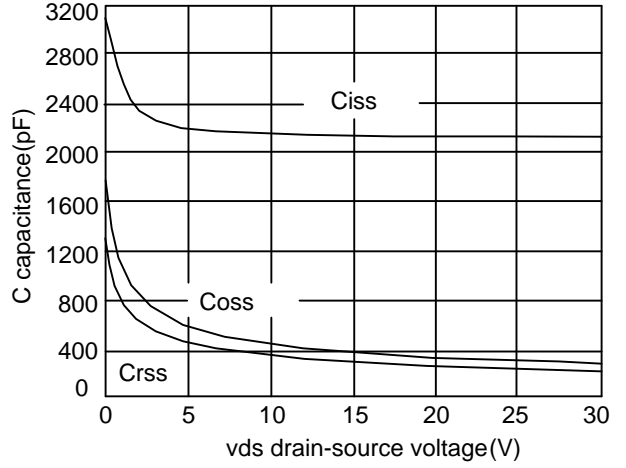


Fig.8 capacitance vs vds

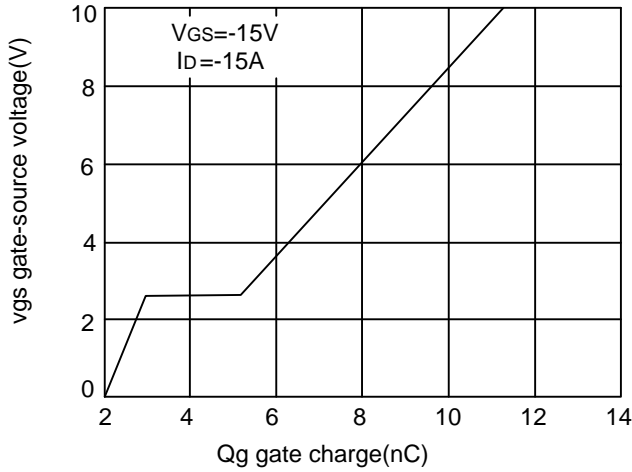


Fig.9 gate charge

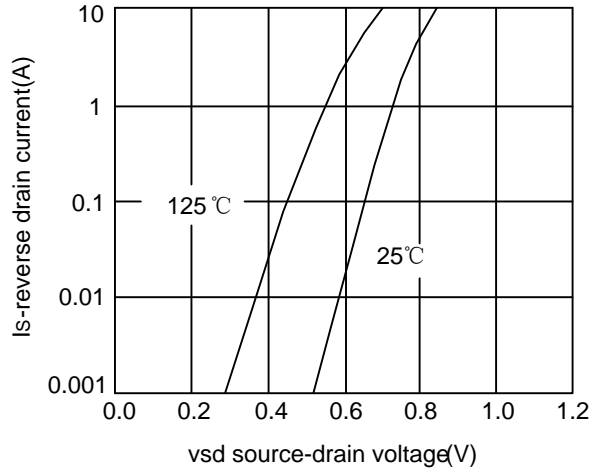


Fig.10 source-drain diode forward

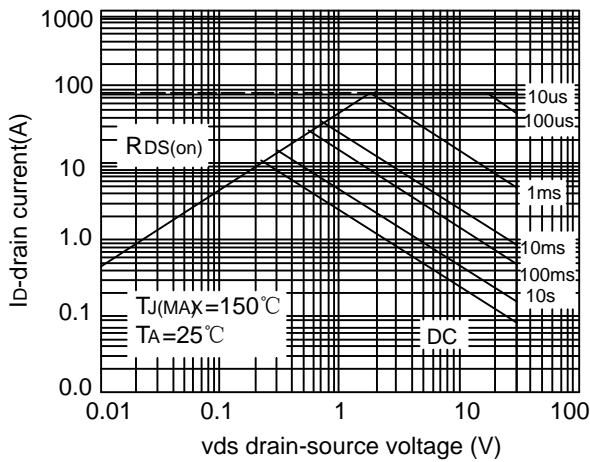


Fig.11 safe operation area

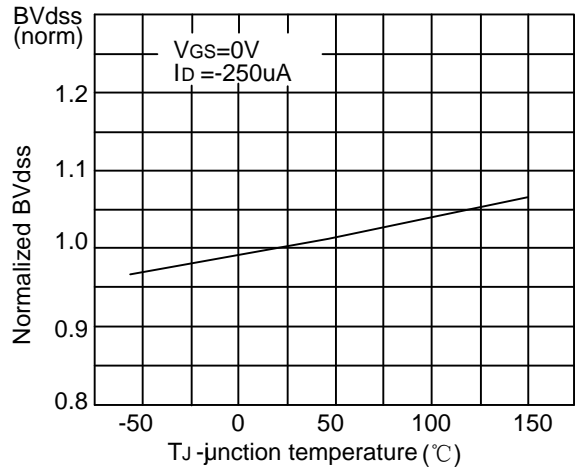
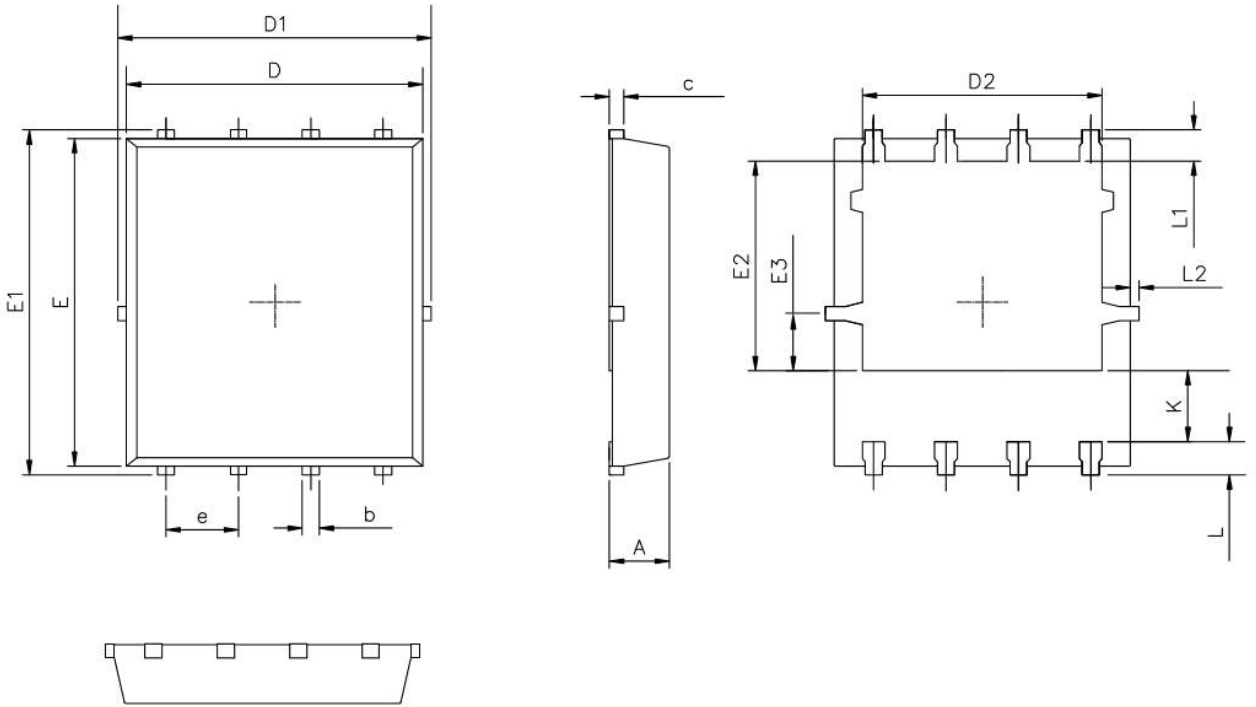
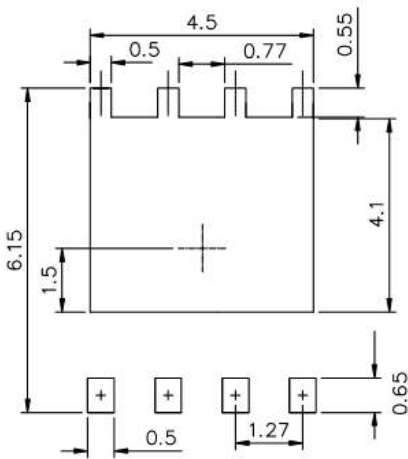


Fig.12 BVdss vs junction temperature

■ PDFN5X6-8L PACKAGE MECHANICAL DATA



RECOMMENDED LAND PATTERN



UNIT:mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50